

# 2SD1273(A)

Rev.F Mar.-2016

## 描述 / Descriptions

TO-220F 塑封封装 NPN 半导体三极管。Silicon NPN transistor in a TO-220F Plastic Package.

## 特征 / Features

$h_{FE}$  高、线性好。

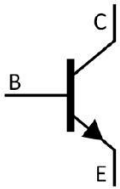
High  $h_{FE}$ , good linearity of  $h_{FE}$ .

## 用途 / Applications

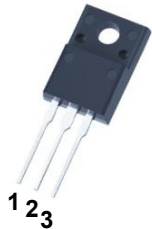
用于高  $h_{FE}$  的功率放大。

Power amplifier with high forward current transfer ratio applications.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : Base

PIN 2 : Collector

PIN 3 : Emitter

## 放大及印章代码 / $h_{FE}$ Classifications & Marking

$h_{FE}$ Classifications Symbol	Q	P	O
$h_{FE}$ Range	500~1000	800~1500	1200~2500

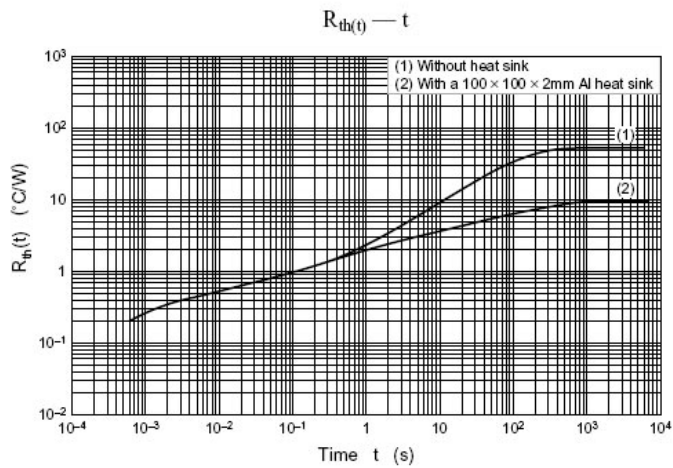
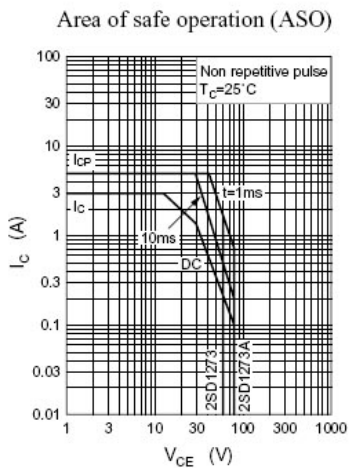
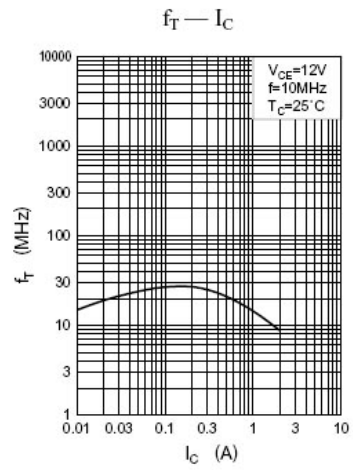
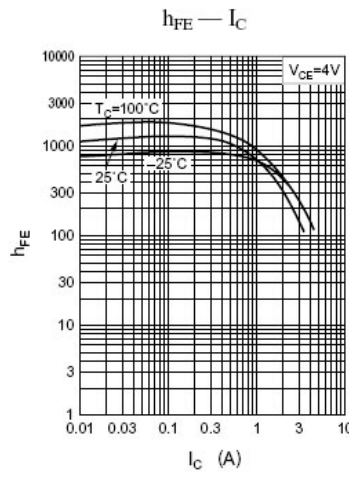
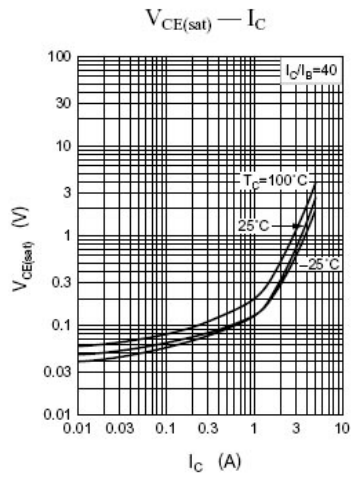
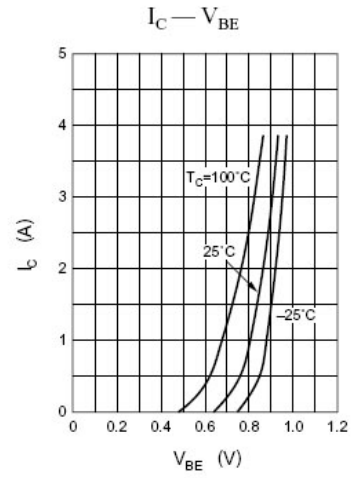
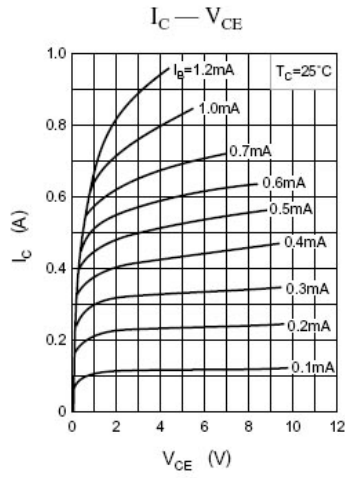
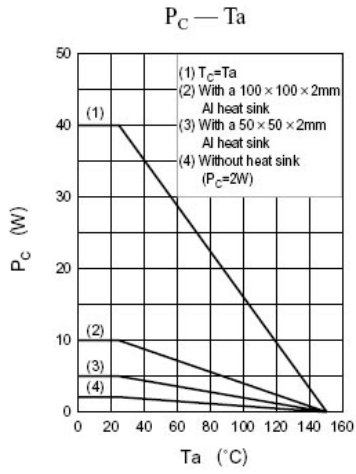
**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit	
Collector to Base Voltage	V <sub>CBO</sub>	2SD1273	80	V
		2SD1273A	100	
Collector to Emitter Voltage	V <sub>CEO</sub>	2SD1273	60	V
		2SD1273A	80	
Emitter to Base Voltage	V <sub>EBO</sub>	6.0	V	
Collector Current - Continuous	I <sub>C</sub>	3.0	A	
Collector Current – Continuous(Pulse)	I <sub>CP</sub>	6.0	A	
Base Current	I <sub>B</sub>	1.0	A	
Collector Power Dissipation	P <sub>C</sub>	2.0	W	
Collector Power Dissipation	P <sub>C</sub> (T <sub>C</sub> =25°C)	40	W	
Junction Temperature	T <sub>j</sub>	150	°C	
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C	

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Emitter Breakdown Voltage	V <sub>CEO</sub>	2SD1273	60			V
		2SD1273A	80			
Collector Cut-Off Current	I <sub>CBO</sub>	2SD1273	V <sub>CB</sub> =80V	I <sub>E</sub> =0	100	μA
Collector Cut-Off Current		2SD1273A	V <sub>CB</sub> =100V	I <sub>E</sub> =0	100	μA
Collector Cut-Off Current	I <sub>CEO</sub>	V <sub>CE</sub> =40V	I <sub>B</sub> =0		100	μA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =6.0V	I <sub>C</sub> =0		100	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =4.0V	I <sub>C</sub> =0.5A	500	2500	
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =2.0A	I <sub>B</sub> =50mA		1.0	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =12V	I <sub>C</sub> =0.2A	f=10MHz	50	MHz

电参数曲线图 / Electrical Characteristic Curve



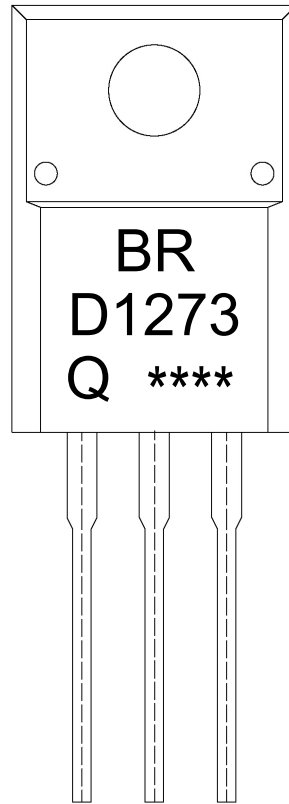
外形尺寸图 / Package Dimensions

T0-220F

单位: mm



印章说明 / Marking Instructions



说明：

BR： 为公司代码

D1273： 为型号代码

Q： 为  $h_{FE}$  分档代码

\*\*\*\*： 为生产批号代码，随生产批号变化。

Note:

BR: Company Code.

D1273: Product Type.

Q:  $h_{FE}$  Classifications Symbol

\*\*\*\*: Lot No. Code, code change with Lot No.

**波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)**



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec；
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec；
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

**使用说明 / Notices**